

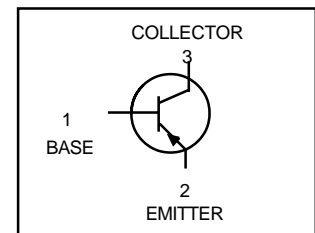
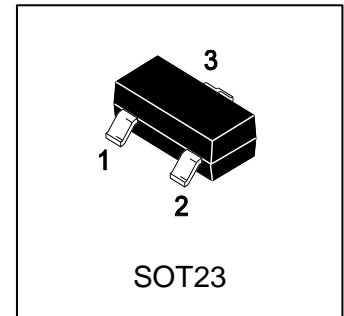
LH8550QLT1G

S-LH8550QLT1G

General Purpose Transistors PNP Silicon

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- High current capacity in compact package.
IC =-1.5A.
- Epitaxial planar type.
- Pb-Free Package is available.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LH8550QLT1G	KIY	3000/Tape&Reel
LH8550QLT3G	KIY	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	VCEO	-50	V
Collector-Base voltage	VCBO	-50	V
Emitter-Base Voltage	VEBO	-6	V
Collector current	IC	-1500	mA

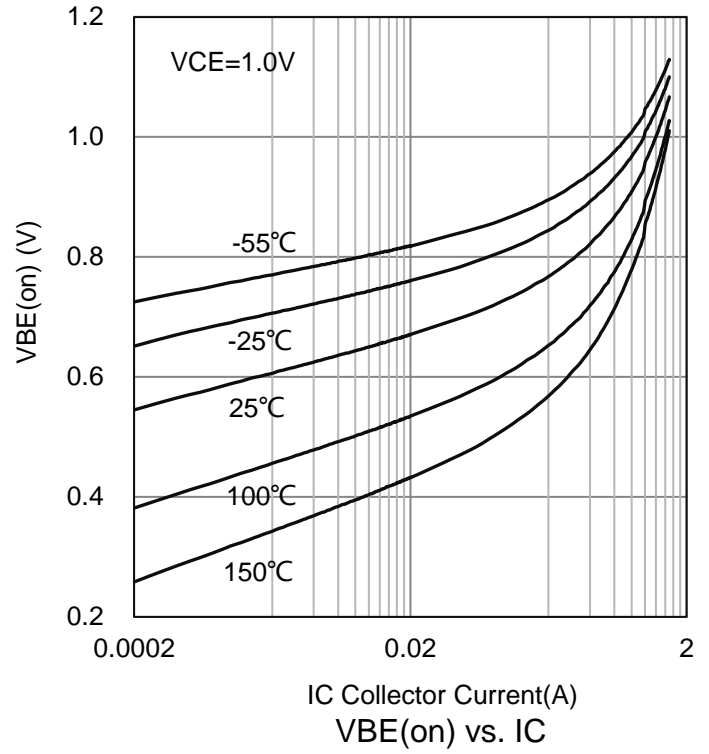
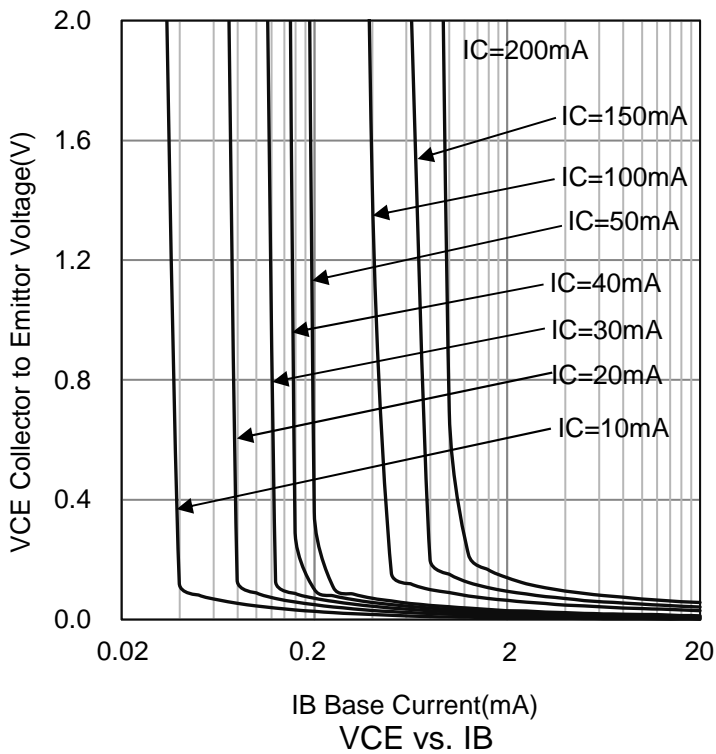
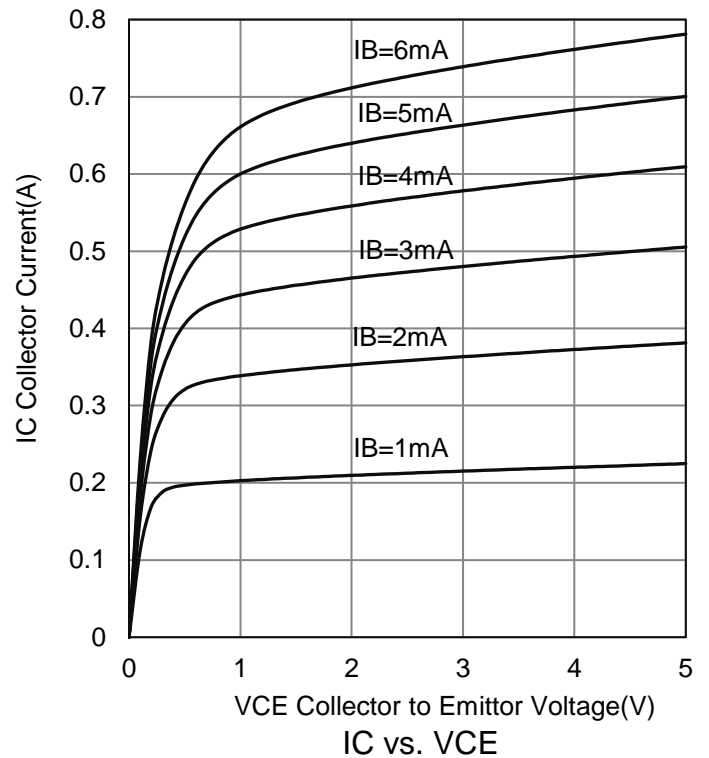
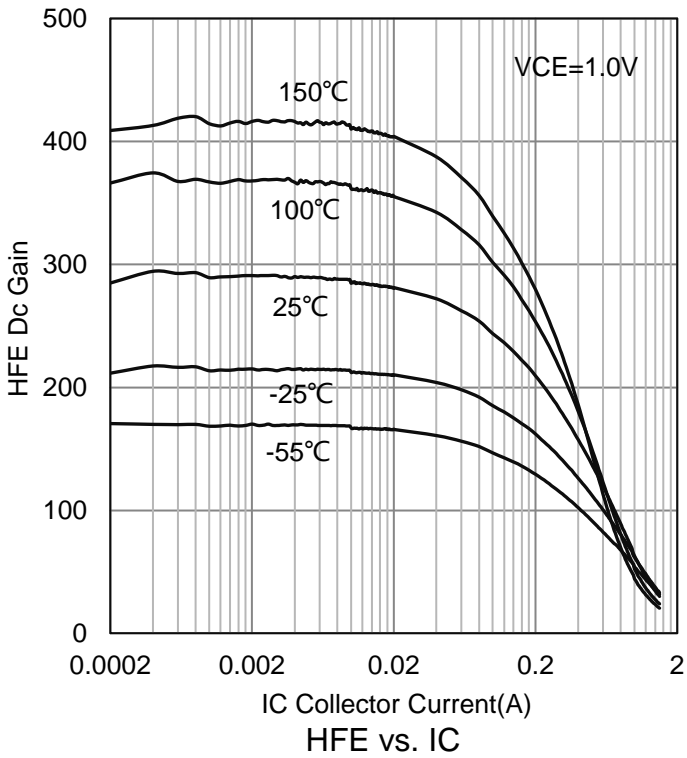
4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Power Dissipation	PD	225	mW
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

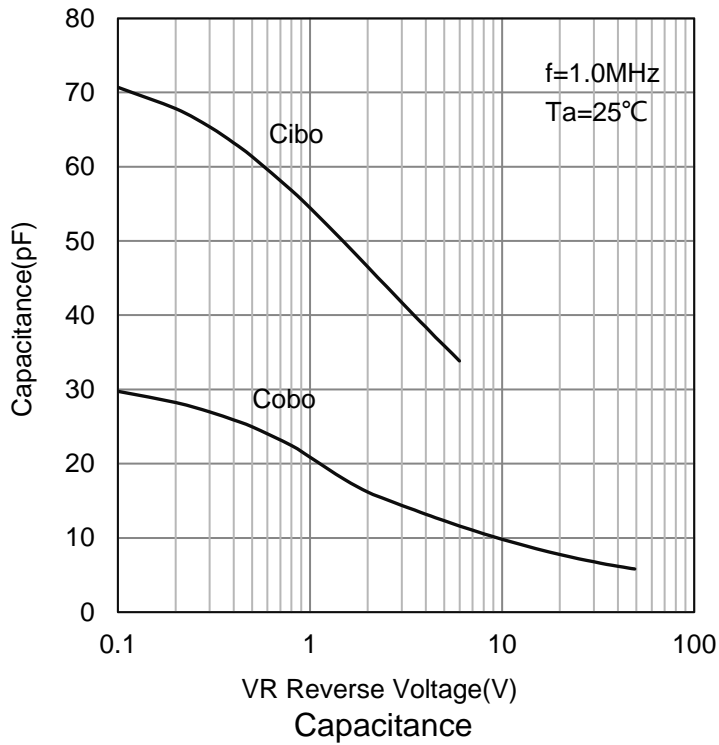
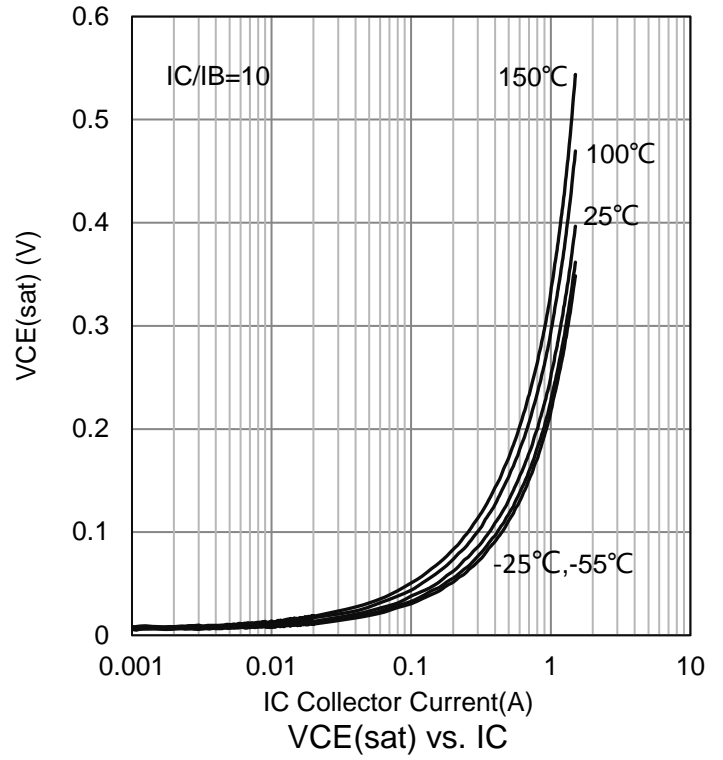
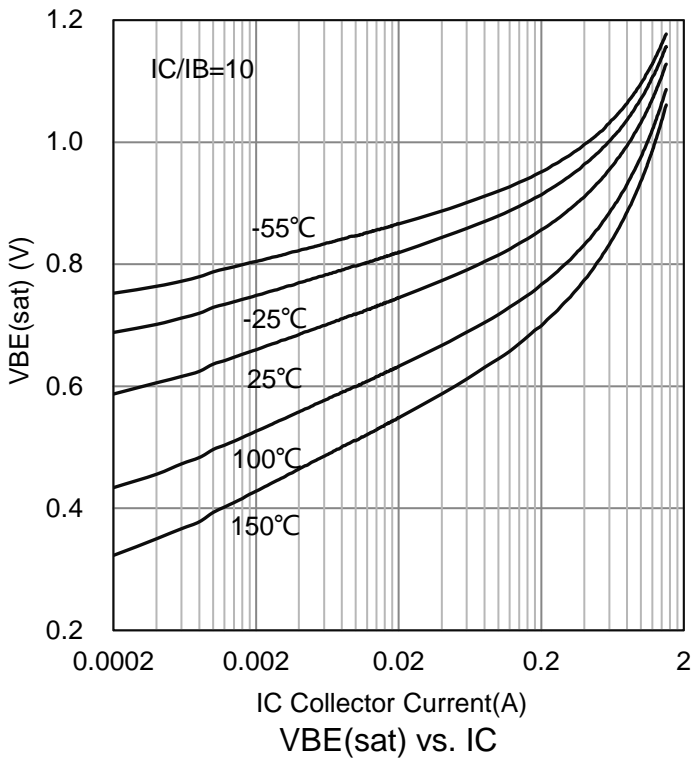
5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage (IC = -2.0mA, IB = 0)	V(BR)CEO	-50	-	-	V
Emitter-Base Breakdown Voltage (IE = -100μA, IC=0)	V(BR)EBO	-6	-	-	V
Collector-Base Breakdown voltage (IC = -100μA, IE=0)	V(BR)CBO	-50	-	-	V
Collector Cutoff Current (VCB = -35 V, IE=0)	ICBO	-	-	-100	nA
Emitter Cutoff Current (VEB = -6V, IC=0)	IEBO	-	-	-100	nA
Base-Emitter Voltage (VCE = -1V, IC = -10mA)	VBE	-	-0.66	-1	V
DC Current Gain (IC = -100mA, VCE = -1V) (IC = -800mA, VCE = -1V)	HFE	160 40	- -	320 -	
Collector-Emitter Saturation Voltage (IC = -800mA, IB = -80mA)	VCE(S)	-	-	-0.5	V
Base-Emitter Saturation Voltage (IC = -800mA, IB = -80mA)	VBE(S)	-	-	-1.2	V

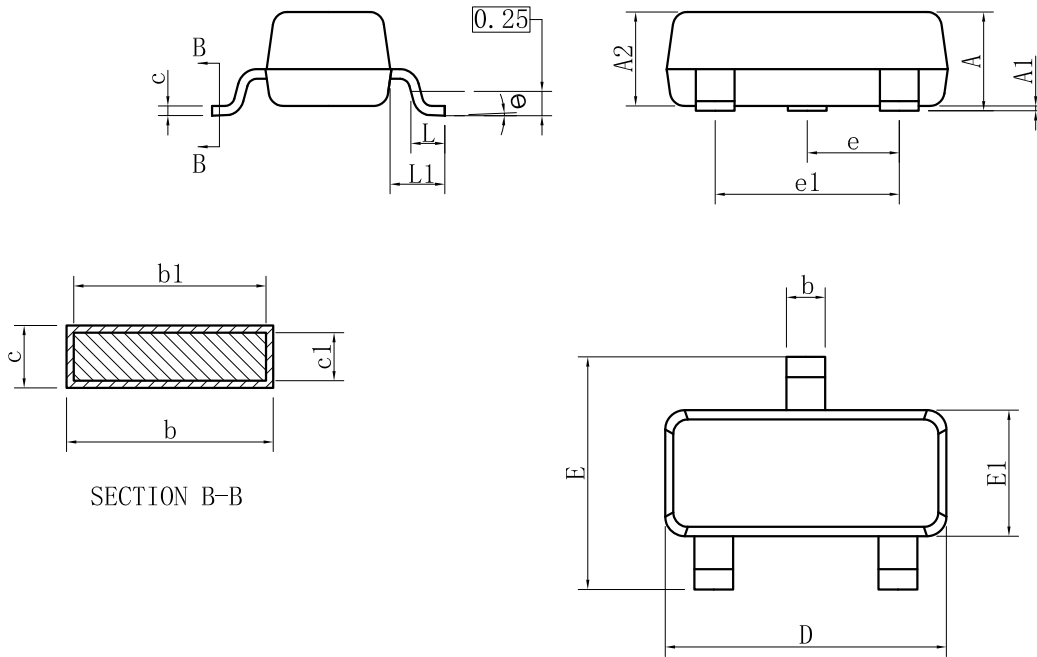
6.ELECTRICAL CHARACTERISTICS CURVES



6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7.OUTLINE AND DIMENSIONS

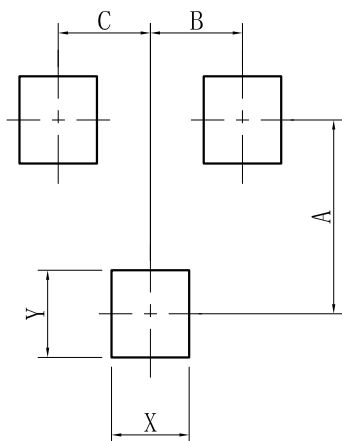


SOT23			
DIM	MIN	NOR	MAX
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.50
b1	0.30	0.40	0.45
c	0.08	-	0.20
c1	0.08	0.10	0.16
D	2.80	2.90	3.04
E	2.10	-	2.64
E1	1.20	1.30	1.40
e	0.95BSC		
e1	1.90BSC		
L	0.40	0.46	0.60
L1	0.54REF		
θ	0°	-	8°
All Dimensions in mm			

GENERAL NOTES

- 1.Top package surface finish Ra0.4±0.2um
- 2.Bottom package surface finish Ra0.7±0.2um
- 3.Side package surface finish Ra0.4±0.2um

8.SOLDERING FOOTPRINT



SOT-23	
DIM	(mm)
X	0.80
Y	0.90
A	2.00
B	0.95
C	0.95

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
- Before you use our Products for new Project, you are requested to carefully read this document and fully understand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC's Products against warning, caution or note contained in this document.
- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)